Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)

ATTY. DOCKET NO. MI30-068	SERIAL NO. Filed herewith
APPLICANT Ji Ung Lee et al.	
FILING DATE Filed Herewith	GROUP Filed Herewith

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
SJF	AA	5,482,870	01/09/96	Inoue			
SJF	AB	5,372,973	12/13/94	Doan et al.			
SJF	AC	5,229,331	07/20/93	Doan et al.			
SJF	AD	5,210,472	05/11/93	Casper et al.			
SJF	AE	4,988,638	01/29/91	Huang et al.			
SJF	AF	6,057,555	5/2/00	Reedy et al.			
SJF	AG	5,710,478	1/20/98	Kanemaru et a.			
SJF	AH	6,020,683	2/1/00	Cathey, Jr. et al.			
SJF	AI	6,249,327 B1	6/19/01	Murade et al.			
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
SJF	AL	5-114734	05/07/93	Japan			X	
SJF	AM	3-194937	08/26/91	Japan			X	
SJF	AN	3-159250	07/09/91	Japan			X	
SJF	AO	A-2-143482	11/24/88	Japan			X	
SJF	AP	61-252687	11/10/88	Japan			X	
SJF	AQ	A-57-85282	11/17/80	Japan			X	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

SJF	AR	Polycrystalline Silicon Thin Film Transistor Incorporating a Semi-Insulating Field Plate for High Voltage Circuitry on Glass,
		F.J. Clough, E.M.S. Narayanan, Y. Chen, W. Eccleston, and W.I. Milne, Appl. Phys. Lett. 71 - 10/06/97, pages 2002-2004, 1997 American Institute of Physics.
SJF	AS	Geometry Dependence of the Transport Parameters in Field Effect Transistors Made From Amorphous Silicon, S. Griep, Mat. Res. Soc. Symp. Proc. 149,
		pages 283-288, 1989 Materials Research Society.
	AT	

EXAMINER	DATE CONSIDERED 1/26/06

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

S:\MI30\068\ID2.wpd A27202051016N